SEMICONDUCTOR LIGHT-EMITTING ELEMENT AND ITS MANUFACTURE

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Applicant:

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- european:

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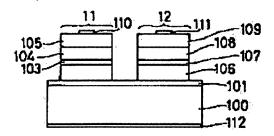
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Abstract of JP6163988

PURPOSE:To obtain a semiconductor light emitting element wherein a plurality of light emitting regions can be formed in a chip, and light emission in a wide wavelength region is realized for a far field pattern and a near field pattern.

CONSTITUTION:Semiconductor layere 11, 12 having light emission regions different in light emission wavelength region are formed on a semiconductor substrate 100. A GaAs substrate is used as the semiconductor substrate 100. The semiconductor layers are formed by using at least one kind out of Al, Ga, In, Zn and Cd, and at least one kind out of P, As, S and Se. The respective light emission regions are formed so as to have different constituent elements or composition ratios. Thereby light emission of wide wavelength regions can be realized for a far field pattern and a near field pattern.



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